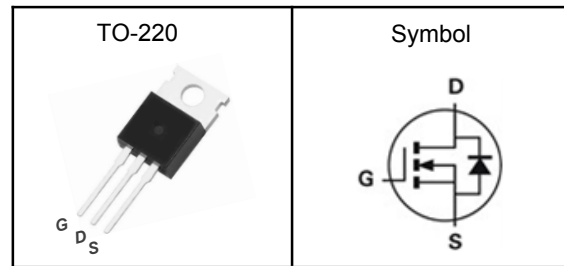


**N-Channel Enhancement Mode MOSFET**
**Features**

- Low  $R_{ds(on)}$  for low conduction loss
- Reliable and Rugged
- ROHS Compliant & Halogen-Free

**Pin Description**

**Applications**

- Power Management in Desktop Computer
- DC/DC Converters

$V_{DSS}$	250	V
$R_{DS(ON)-Typ}$	16	m $\Omega$
$I_D$	70	A

**Absolute Maximum Ratings** ( $T_J=25^\circ\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	250	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$T_J$	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$E_{AS}$	Single Pulse Avalanche Energy <sup>3</sup>	2000	mJ
$I_{DM}^{①}$	300 $\mu\text{s}$ Pulse Drain Current Tested	280	A
$I_D$	Continuous Drain Current	$T_C=25^\circ\text{C}$ 70	A
$P_D$	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 250	W

**Thermal Characteristics**

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	0.5	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature  $150^\circ\text{C}$ .

Note ③ : Surface Mounted on  $1\text{in}^2$  FR-4 board with 1oz.



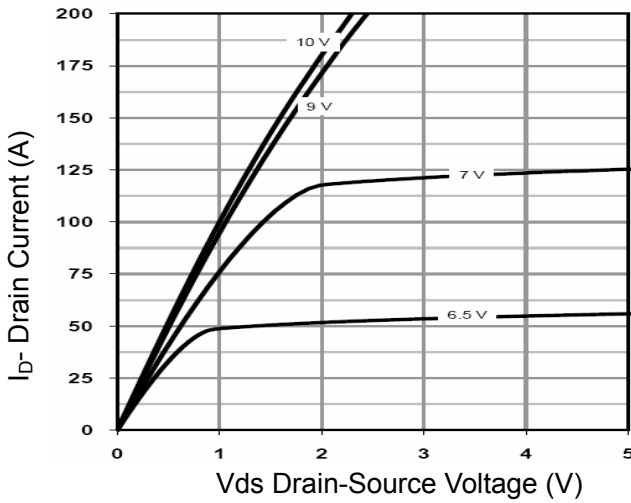
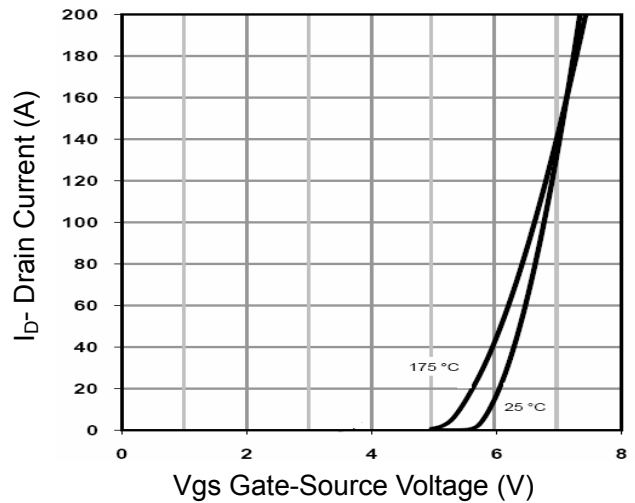
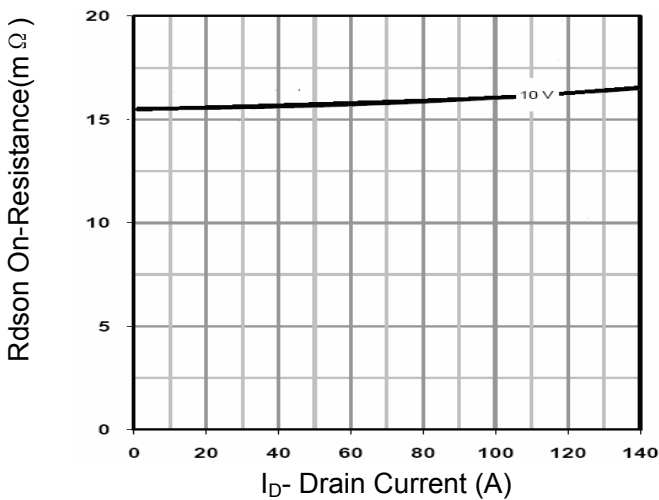
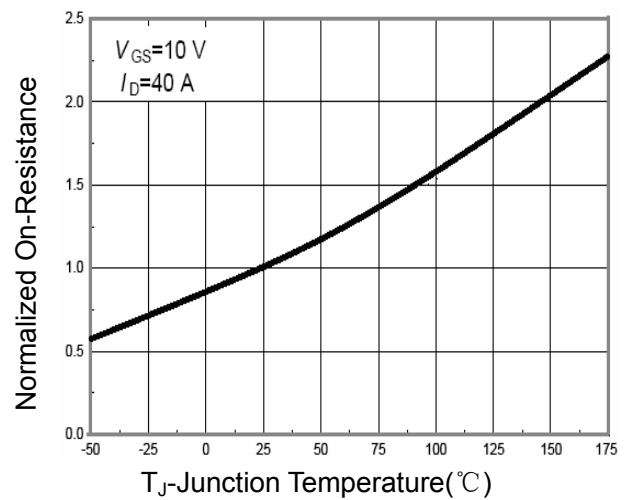
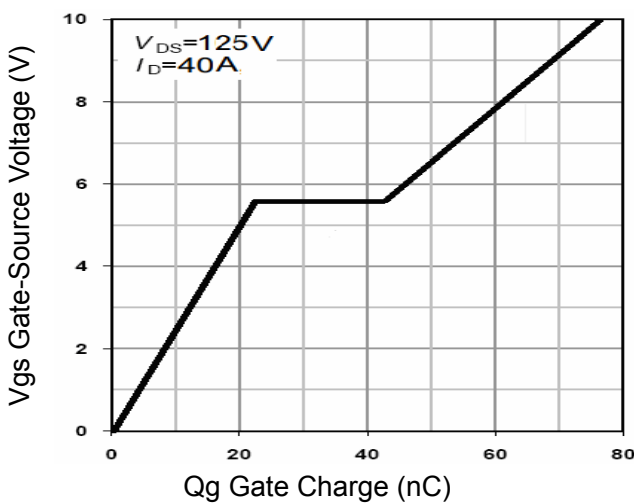
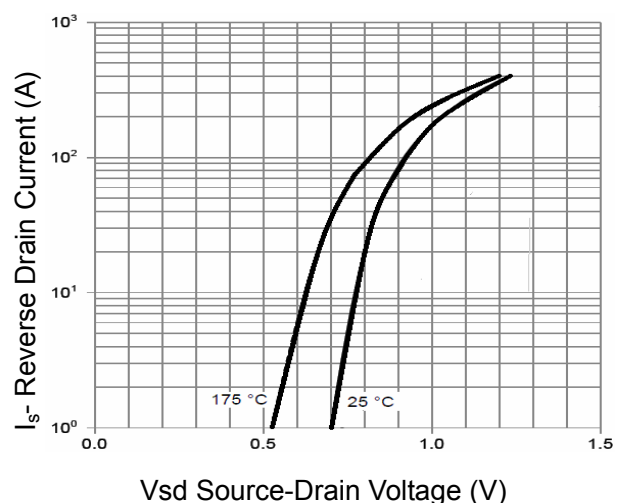
**N-Channel Enhancement Mode MOSFET**

**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)

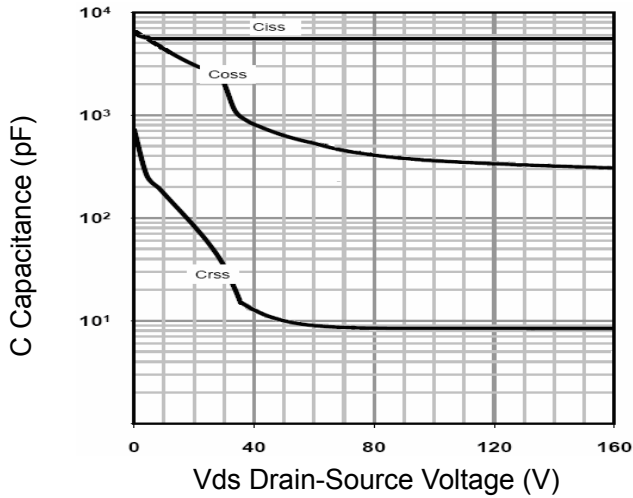
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Static Electrical Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	250	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=250V, V_{GS}=0V$	---	---	1	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	---	4.5	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=35A$	---	16	20	$m\Omega$
<b>Dynamic Characteristics</b> <sup>⑤</sup>						
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=125V,$ $Freq.=1MHz$	---	6535	---	pF
$C_{oss}$	Output Capacitance		---	280	---	
$C_{riss}$	Reverse Transfer Capacitance		---	12	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=125V, I_D=40A$ $V_{GS}=10V, R_G=4.7\Omega$	---	18	---	nS
$T_r$	Turn-on Rise Time		---	26	---	
$T_{d(off)}$	Turn-off Delay Time		---	48	---	
$T_f$	Turn-off Fall Time		---	11	---	
$Q_g$	Total Gate Charge	$V_{DS}=125V,$ $V_{GS}=10V,$ $I_D=40A$	---	78	---	nC
$Q_{gs}$	Gate-Source Charge		---	23	---	
$Q_{gd}$	Gate-Drain Charge		---	18	---	
<b>Source-Drain Characteristics</b> ( $T_J=25^{\circ}\text{C}$ )						
$V_{SD}$ <sup>④</sup>	Diode Forward Voltage	$I_S=40A, V_{GS}=0V$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=40A,$	---	146	---	nS
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	560	---	nC

Note ④ : Pulse test (pulse width $\leq$ 300 $\mu s$ , duty cycles $\leq$ 2%).

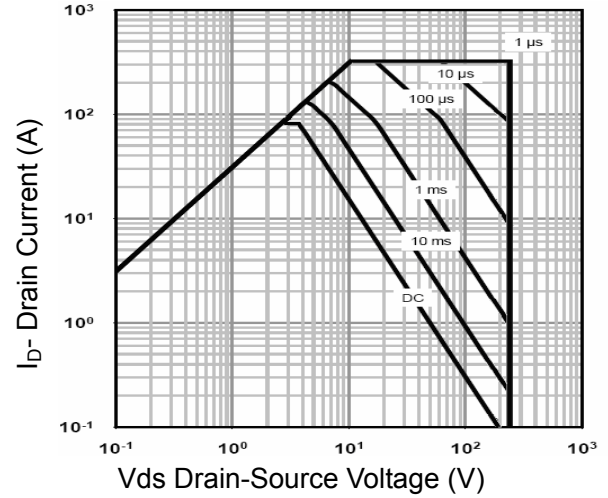
Note ⑤ : Guaranteed by design, not subject to production testing.

**N-Channel Enhancement Mode MOSFET**
**Typical Characteristics**

**Figure 1 Output Characteristics**

**Figure 2 Transfer Characteristics**

**Figure 3 Rdson- Drain Current**

**Figure 4 Rdson-Junction Temperature**

**Figure 5 Gate Charge**

**Figure 6 Source- Drain Diode Forward**

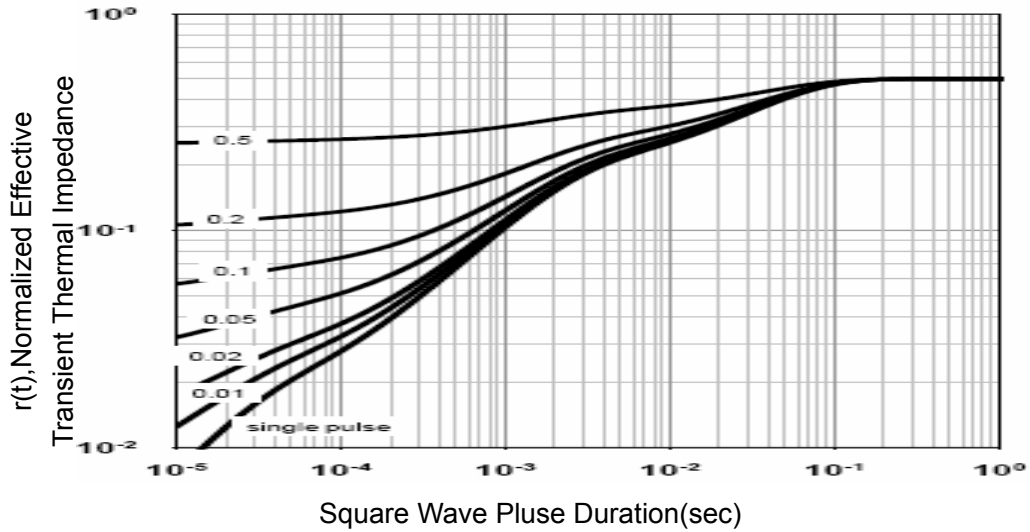
**N-Channel Enhancement Mode MOSFET**



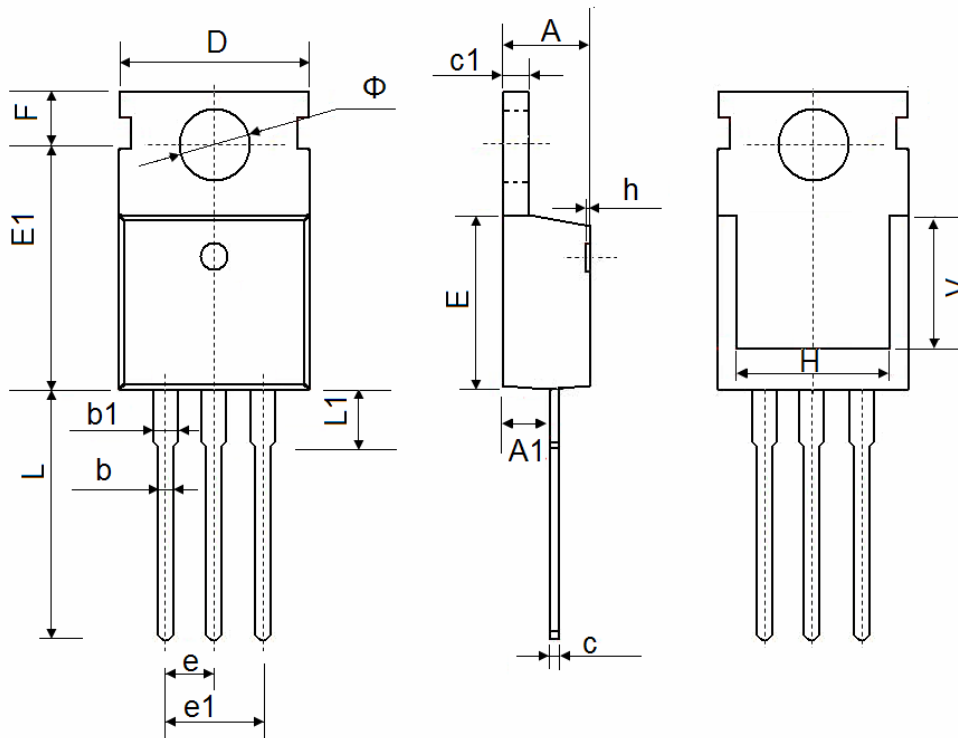
**Figure 7 Capacitance vs Vds**



**Figure 8 Safe Operation Area**



**Figure 9 Normalized Maximum Transient Thermal Impedance**

**N-Channel Enhancement Mode MOSFET**
**TO-220 Package Outline Data**


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.350	4.650
A1	2.250	2.550
b	0.710	0.910
b1	1.170	1.400
c	0.330	0.650
c1	1.200	1.400
D	9.910	10.250
E	8.9500	9.750
E1	12.650	12.950
e	2.540 TYP.	
e1	4.980	5.180
F	2.650	2.950
H	7.900	8.100
h	0.000	0.300
L	12.700	13.500
L1	2.850	3.250
V	7.500 REF.	
Φ	3.400	3.800